

# Kinematical studies of the glass transition in glassy $\text{Se}_{80-x}\text{Te}_{20}\text{Sb}_x$ \*

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The present paper reports kinematic studies of the glass transition in glassy  $\text{Se}_{80-x}\text{Te}_{20}\text{Sb}_x$  alloys using the differential scanning calorimetric technique. The glass transition temperature ( $T_g$ ) is found to increase monotonically with the heating rate.  $T_g$  also increases with the increase of Sb concentration in ternary  $\text{Se}_{80-x}\text{Te}_{20}\text{Sb}_x$  system. From the heating rate dependence of glass transition temperature, the activation energy ( $\Delta E_t$ ) for the relaxation time controlling the structural enthalpy, is calculated. The composition dependence of  $T_g$  and  $\Delta E_t$  is discussed in terms of the structure of the Se-Te-Sb glassy system. © 2000 Kluwer Academic Publishers

## 1. Introduction

Chalcogenide glasses have attracted a great deal of attention because of their technical importance in various solid state devices. It is well known [1–4] that thermal relaxation occurs in a glassy substance following an instantaneous change in temperature (during the quenching process), as it relaxes from a state of higher enthalpy towards a metastable equilibrium state of lower enthalpy. This type of thermal relaxation depends upon the annealing temperature and may be quite fast near the glass transition temperature. The glass transition is exhibited in Differential Thermal Analyser (DTA) or Differential Scanning Calorimetry (DSC) traces as an endothermic peak or a shift in the base line due to a change in specific heat. However, in chalcogenide glasses, such an endothermic peak can also be observed due to a fast change in enthalpy when the glassy system relaxes quickly due to a decrease in viscosity at the glass transition temperature. DTA or DSC techniques can, therefore, be quite useful in the study of thermal relaxation in glasses.

Among chalcogenide glasses, Se-Te alloys have gained much importance because of their higher photo-sensitivity, greater hardness, higher crystallization temperature, and smaller aging effects as compared to pure Se glass. The effect of incorporation of Sb on the electrical properties of these alloys has been studied by various workers [5–10]. In general, it is observed that the dc conductivity increases, the activation energy for dc conduction decreases, the thermoelectric power decreases, and the photoconductive decay becomes slower on incorporation of Sb to the binary  $\text{Se}_{80}\text{Te}_{20}$  alloy. To explain the above results it is generally assumed that the addition of Sb in the Se-Te system leads to a cross-linking of Se-Te chains which enhances the disorder in

the system and hence leads to a deeper penetration of the localized state into the energy gap.

The present paper reports the kinematic studies of glass transition in  $\text{Se}_{80-x}\text{Te}_{20}\text{Sb}_x$  alloys using DSC technique with a view to understand the thermal relaxation phenomena in these glasses. From the heating rate dependence of glass transition temperature, the activation energy of molecular motions and rearrangement near glass transition temperature  $T_g$  is calculated and its composition dependence is discussed in terms of the structure of  $\text{Se}_{80-x}\text{Te}_{20}\text{Sb}_x$ .

## 2. Experimental

Glassy alloys of  $\text{Se}_{80-x}\text{Te}_{20}\text{Sb}_x$  where  $x = 0, 5, 10, 15$  have been prepared by a quenching technique. High purity materials (5N pure) Se, Te and Sb in appropriate atomic percent were weighed and sealed in quartz ampoules (Length = 5 cm and internal diameter = 8 mm) in a vacuum of  $10^{-2}$  Pascal. The sealed ampoules were kept inside the furnace at  $600^\circ\text{C}$  (The temp. was raised at a rate of 3 to 4 K/min) for 10–12 h and rocked frequently to make the melt homogeneous. The quenching was done in the water. Glasses thus prepared were ground to make a fine powder for DSC studies. In DSC, the sample is heated at constant rate and the changes in heat flow with respect to an empty reference pan were measured. The samples were kept at room temperature ( $\sim 300$  K) in dark for about one month for the attainment of thermodynamic equilibrium as stressed by Abkowitz [1] in chalcogenide glasses.

DSC 2910 Differential Scanning Calorimeter (T.A. instrument, USA) was used at four different heating rates 5, 10, 15 and  $20^\circ\text{C}/\text{min}$  for the above studies.

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### 3. Results

Figs 1–4 show typical DSC thermograms at different heating rates in glassy alloy  $\text{Se}_{80-x}\text{Te}_{20}\text{Sb}_x$  ( $x = 0, 5, 10$  and  $15$ ). These figures indicate that well defined endothermic peaks are observed at the glass transition temperature ( $T_g$ ) rather than a shift in the base line. At higher temperatures, a exothermic peak was also observed which represents the crystallization temperature ( $T_c$ ). It also indicated that  $T_g$  and  $T_c$  both shift to higher temperatures as the heating rate is increased from  $5$  to  $20^\circ\text{C}/\text{min}$ . The values of  $T_g$  at different heating rates for various glassy alloys are noted from the DSC traces, i.e., the temperatures at which endother-

mic peaks occur. Such values are given in Table I and plotted in Fig. 5. Table I shows that the value of  $T_g$  at a particular heating rate increases with the increase of Sb concentration in  $\text{Se}_{80-x}\text{Te}_{20}\text{Sb}_x$  ( $x = 0, 5, 10$  and  $15$ ) glassy system.

The heating rate dependence of the glass transition temperature in chalcogenide glasses is interpreted in terms of thermal relaxation phenomena. In this kinetic interpretation the enthalpy at a particular temperature and time  $H(T, t)$  of the glassy system, after an instantaneous isobaric change in temperature, relaxes isothermally towards a new equilibrium value  $H_c(T)$ . The relaxation equation can be written in the following

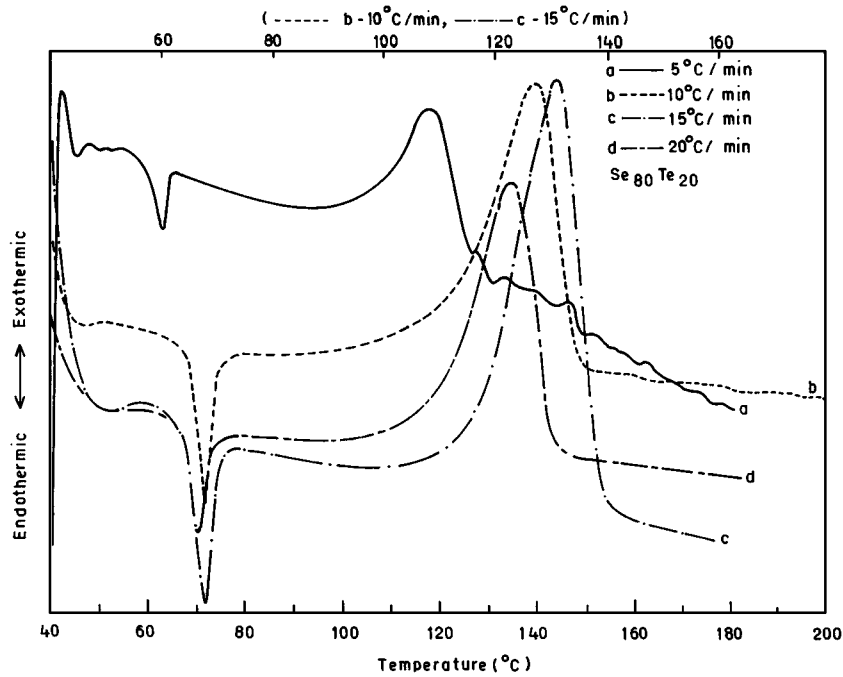


Figure 1 DSC thermograms at different heating rates of  $\text{Se}_{80}\text{Te}_{20}$ .

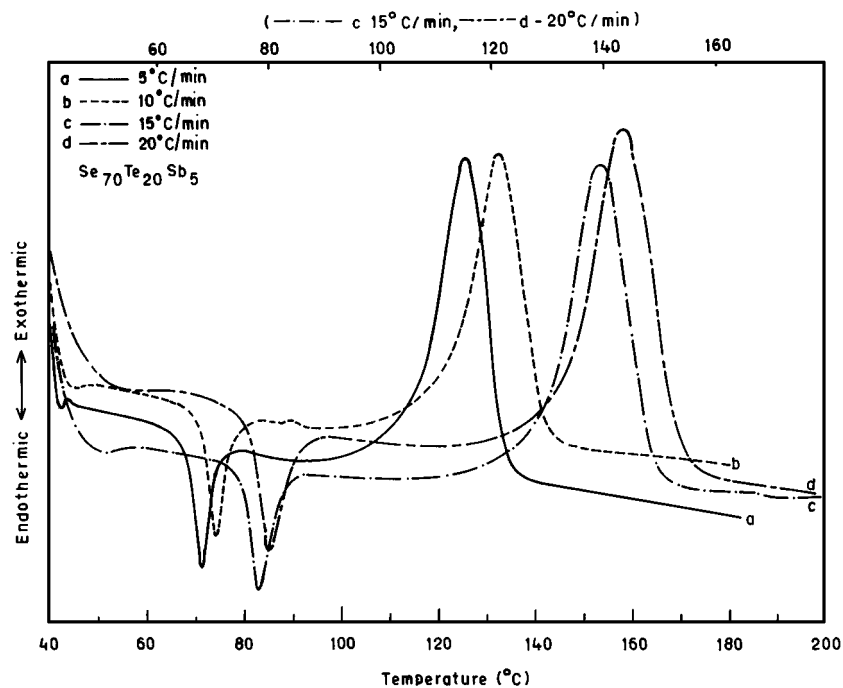


Figure 2 DSC thermograms at different heating rates of  $\text{Se}_{75}\text{Te}_{20}\text{Sb}_5$ .

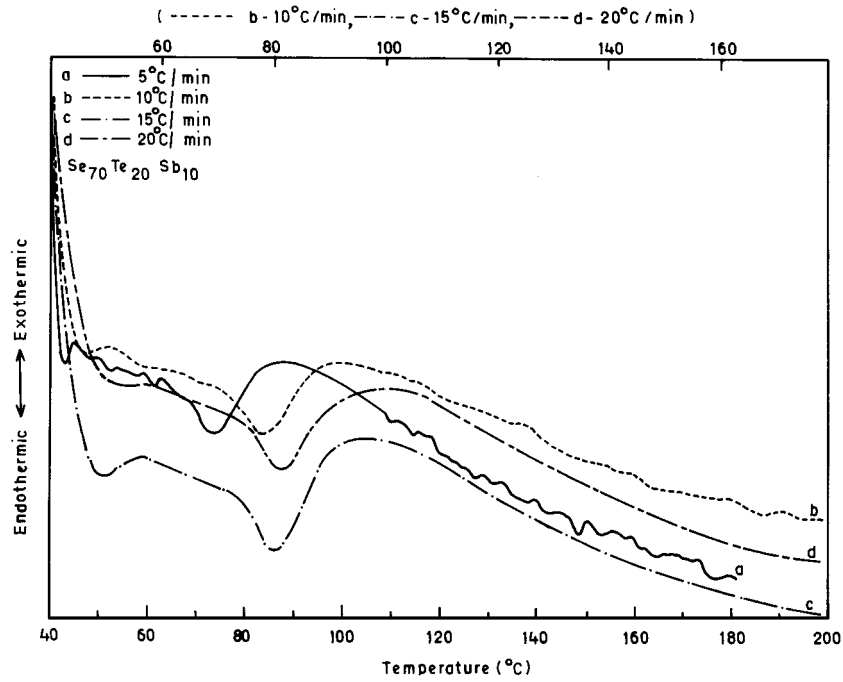


Figure 3 DSC thermograms at different heating rates of  $\text{Se}_{70}\text{Te}_{20}\text{Sb}_{10}$ .

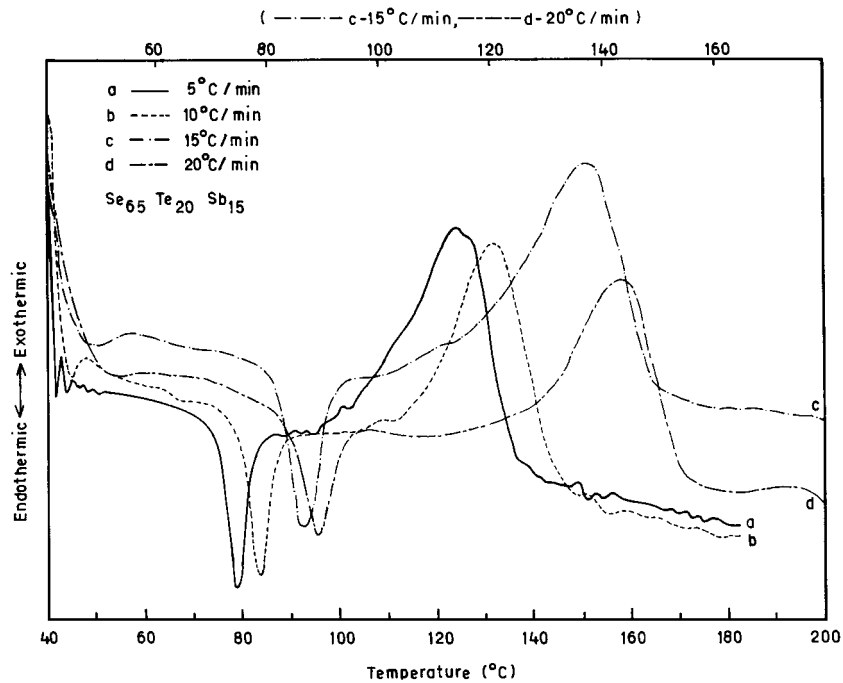


Figure 4 DSC thermograms at different heating rates of  $\text{Se}_{65}\text{Te}_{20}\text{Sb}_{15}$ .

TABLE I The values of glass transition temperature ( $T_g$ ) in  $^{\circ}\text{C}$  in  $\text{Se}_{80-x}\text{Te}_{20}\text{Sb}_x$  ( $x = 0, 5, 10$  and  $15$ ) at different heating rates

Samples	Heating rates			
	5 $^{\circ}\text{C}/\text{min}$	10 $^{\circ}\text{C}/\text{min}$	15 $^{\circ}\text{C}/\text{min}$	20 $^{\circ}\text{C}/\text{min}$
$\text{Se}_{80}\text{Te}_{20}$	63.8 $^{\circ}\text{C}$	68.0 $^{\circ}\text{C}$	69.3 $^{\circ}\text{C}$	71.1 $^{\circ}\text{C}$
$\text{Se}_{75}\text{Te}_{20}\text{Sb}_5$	71.5 $^{\circ}\text{C}$	74.9 $^{\circ}\text{C}$	77.3 $^{\circ}\text{C}$	80.0 $^{\circ}\text{C}$
$\text{Se}_{70}\text{Te}_{20}\text{Sb}_{10}$	74.6 $^{\circ}\text{C}$	74.6 $^{\circ}\text{C}$	80.6 $^{\circ}\text{C}$	82.0 $^{\circ}\text{C}$
$\text{Se}_{65}\text{Te}_{20}\text{Sb}_{15}$	79.3 $^{\circ}\text{C}$	82.1 $^{\circ}\text{C}$	86.0 $^{\circ}\text{C}$	88.7 $^{\circ}\text{C}$

form [5]:

$$\left(\frac{\delta H}{\delta t}\right)_T = -\frac{(H - H_c)}{\tau} \quad (1)$$

where  $\tau$  is a temperature dependent structural relaxation time and is given by the following relation

$$\tau = \tau_0 \exp\left(\frac{-\Delta E_t}{RT}\right) \exp[-c(H - H_c)] \quad (2)$$

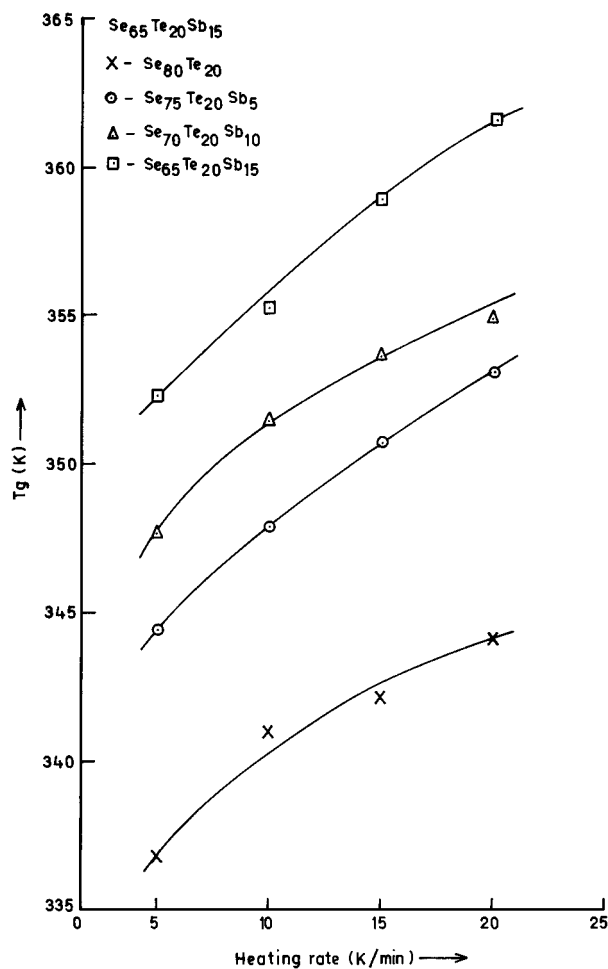


Figure 5 Variation of glass transition temperature ( $T_g$ ) with heating rates ( $\beta$ ) in  $\text{Se}_{80-x}\text{Te}_{20}\text{Sb}_x$  ( $x = 0, 5, 10$  and  $15$ ).

where  $\tau_0$  and  $c$  are constants and  $\Delta E_t$  is the activation energy of relaxation time. Using the above equations, it can be shown that

$$\frac{d \ln \beta}{d\left(\frac{1}{T_g}\right)} = \frac{-\Delta E_t}{R} \quad (3)$$

Equation 3 states that  $\ln \beta$  vs.  $1/T_g$  plot should be straight line and the activation energy involved in the molecular motions and rearrangements around  $T_g$  can be calculated from the slope of this plot.

Fig. 6 shows  $\ln \beta$  vs.  $1000/T_g$  curves for various glassy alloys in  $\text{Se}_{80-x}\text{Te}_{20}\text{Sb}_x$  system. In the present case such plots are straight lines and the values of  $\Delta E_t$  are calculated from the slopes of the curves shown in Fig. 6.

The results of these calculations are given in Table II. These results show that  $\Delta E_t$  first decreases and then increases with an increase of Sb concentration (See Fig. 7).

#### 4. Discussion

The glass transition temperature ( $T_g$ ) of chalcogenide glasses shows coordination number dependence [11] which in turn depends on the percentage of the substituent atom [12]. The glass transition temperature of

TABLE II Composition dependence of the activation energy of relaxation time  $\Delta E_t$

Sample	$\Delta E_t$ in KJ/mol
$\text{Se}_{80}\text{Te}_{20}$	174
$\text{Se}_{75}\text{Te}_{20}\text{Sb}_5$	133
$\text{Se}_{70}\text{Te}_{20}\text{Sb}_{10}$	167
$\text{Se}_{65}\text{Te}_{20}\text{Sb}_{15}$	208

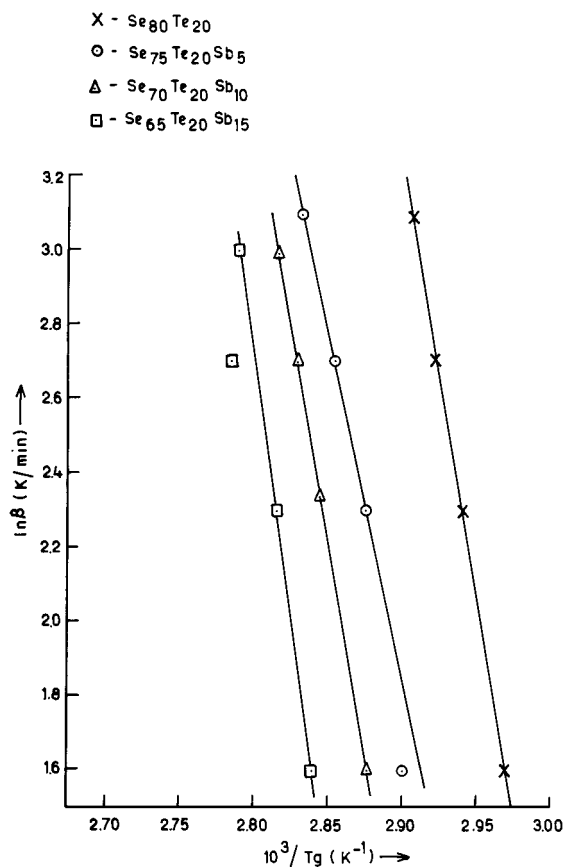


Figure 6 Heating rate dependence of glass transition temperature by a plot of  $\ln \beta$  vs.  $10^3/T_g$ .

the system  $\text{Se}_{80-x}\text{Te}_{20}\text{Sb}_x$  ( $x = 0, 5, 10$  and  $15$ ) increases linearly with increasing Sb concentration as shown in Fig. 8 and follows a relation:

$$\ln T_g = aZ + b \quad (4)$$

where  $Z$  denotes the average coordination number [13] per atom (calculated in terms of covalent bonding). Equation 4 is similar to the empirical relation proposed by Tanaka [14]. The constant 'a' is positive showing the increase of  $T_g$  with  $Z$ . The atomic percentage of Sb atom has also been marked in Fig. 8. The results obtained from Fig. 8 are quite consistent with the experimental data.

The increasing trend of  $T_g$  with increasing Sb impurity in our system may be explained by considering the structural change due to the introduction of Sb atoms. Glassy Se shows both chain and ring structures [15].

An introduction of Te decreases the Se ring concentration favouring Se-Te mixed rings. A slight increase in polymeric chain of Se is also observed. Sb which

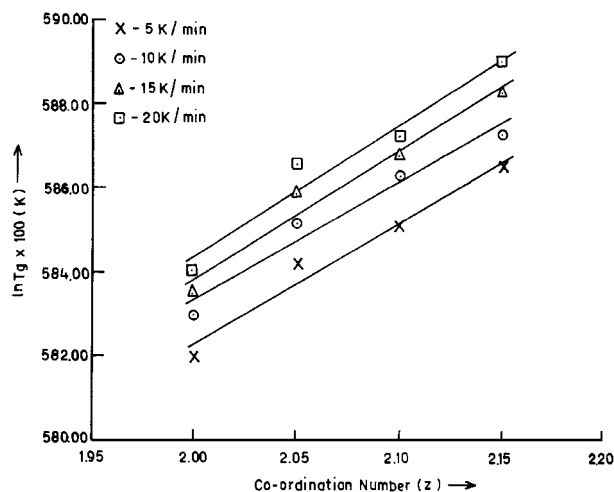


Figure 7 Composition dependence of the activation energy for thermal relaxation ( $\Delta E_t$ ).

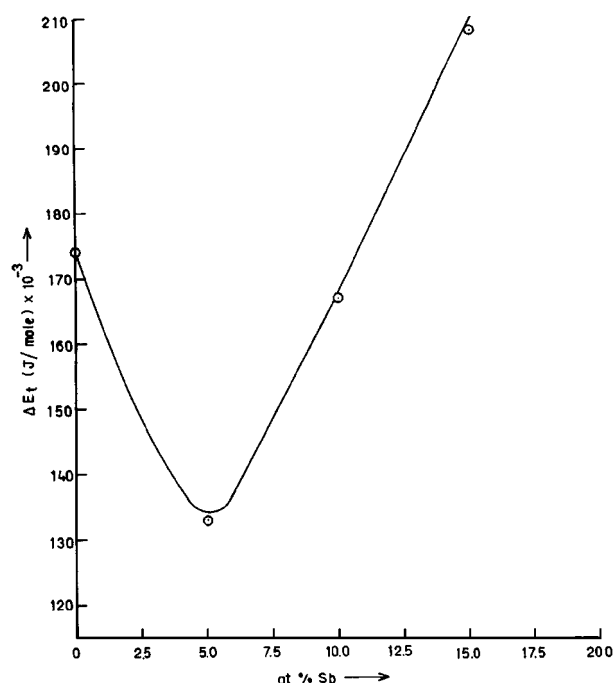


Figure 8 Variation of glass transition temperature ( $T_g$ ) with average co-ordination number ( $Z$ ).

belongs to group V of periodic table when added to the above system may break the Se-Te chains or Se-Te mixed rings to satisfy its coordination number and form a cross linked structure. The addition of Sb also causes a

decrease of  $\text{Se}_8$  rings and increase chain length [15–17]. Hence  $T_g$  increases with increasing Sb concentration.

## 5. Conclusion

Glass transition temperature has been determined from DSC scans at different heating rates in four glassy samples in  $\text{Se}_{80-x}\text{Te}_{20}\text{Sb}_x$  system. In all the glassy alloys,  $T_g$  increases monotonically with the increase of heating rate. The activation energy [ $\Delta E_t$ ] of molecular motions and rearrangements around glass transition temperature is determined from the heating rate dependence of  $T_g$ .  $\Delta E_t$  is found to be composition dependent.  $T_g$  also increases on the addition of Sb to binary  $\text{Se}_{80}\text{Te}_{20}$  alloy. A correlation of  $T_g$  with the increase in coordination number is established. The increase in  $T_g$  is explained in terms of the cross-linked structure in Se-Te-Sb system [15].

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